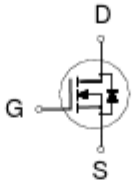
杰力科技股份有限公司
Excelliance MOS Corporation

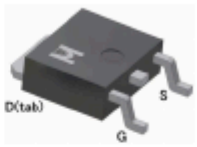
EMBA5N10A

N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	100V
$R_{DSON\ (MAX.)}$	150mΩ
I_D	10A





UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	10	A
	T_C = 100 °C		7	
Pulsed Drain Current[1]		I_{DM}	40	
Avalanche Current		I_{AS}	12	
Avalanche Energy	L = 0.1mH, ID=12A, RG=25Ω	E_{AS}	7.2	mJ
Repetitive Avalanche Energy[2]	L = 0.05mH	E_{AR}	3.6	
Power Dissipation	T_C = 25 °C	P_D	30	W
	T_C = 100 °C		12	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		4.2	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle ≤ 1%